

METHOD FOR FABRICATING CRYSTALLINE-DIELECTRIC THIN FILMS AND DEVICES FORMED USING SAME

ABSTRACT OF THE DISCLOSURE

This invention describes a new method for forming and depositing thin films of crystalline dielectric materials. The present technique uses chemical synthesis to control the granularity and thickness of the dielectric films. This method has several key advantages over existing technologies, and facilitates the integration of crystalline dielectric materials into high-density memory devices.